

## Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected up to 2kV**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 standards for High Reliability**



ESD protected up to 2kV

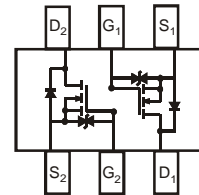


TOP VIEW



BOTTOM VIEW

SOT-26


 TOP VIEW  
Internal Schematic

## Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.015 grams (approximate)

## Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	50	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current (Note 1)	$I_D$	Continuous	305
		Pulsed (Note 3)	800

## Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	400	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	313	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-65 to +150	$^\circ\text{C}$

## Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	50	—	—	V	$V_{GS} = 0V, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current @ $T_C = 25^\circ\text{C}$	$I_{DSS}$	—	—	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	1	$\mu\text{A}$	$V_{GS} = \pm 12V, V_{DS} = 0V$
				500	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$
50	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$				
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.49	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	3.0	$\Omega$	$V_{GS} = 1.8V, I_D = 50\text{mA}$
				2.5	$\Omega$	$V_{GS} = 2.5V, I_D = 50\text{mA}$
				2.0	$\Omega$	$V_{GS} = 5.0V, I_D = 50\text{mA}$
On-State Drain Current	$I_{D(ON)}$	0.5	1.4	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	$V_{SD}$	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	—	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	—	5.0	pF	

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposefully added lead.
  3. Pulse width  $\leq 10\mu\text{s}$ , Duty Cycle  $\leq 1\%$ .
  4. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  5. Short duration pulse test used to minimize self-heating effect.

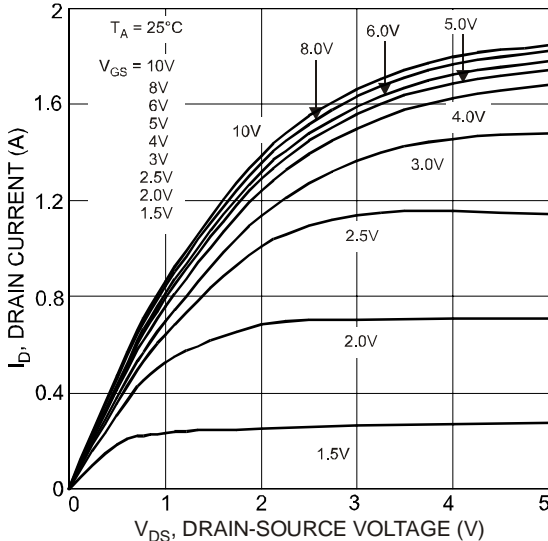


Fig. 1 Typical Output Characteristics

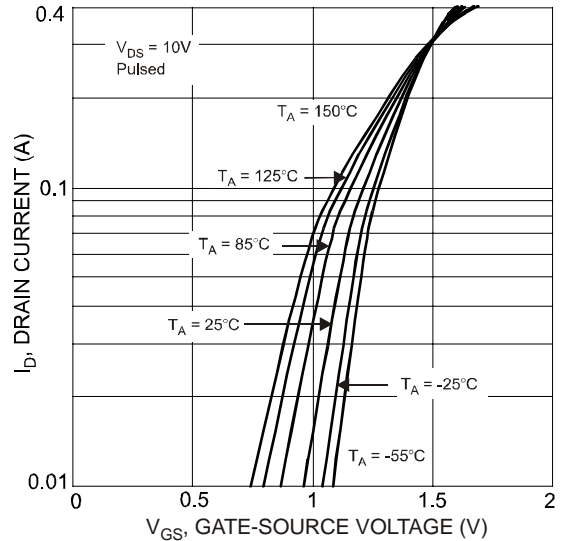


Fig. 2 Typical Transfer Characteristics

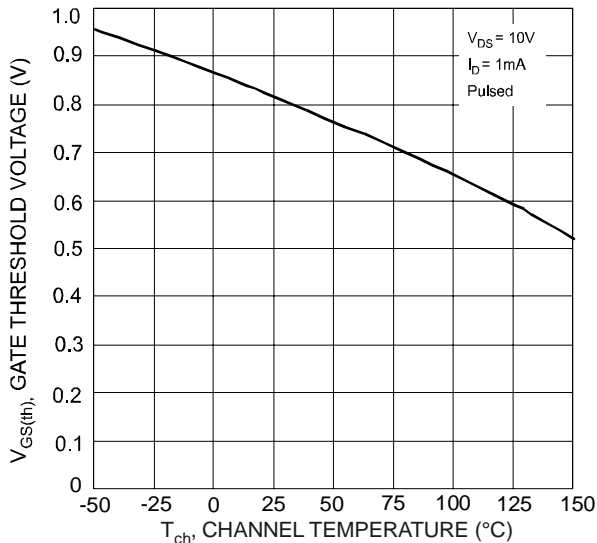


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

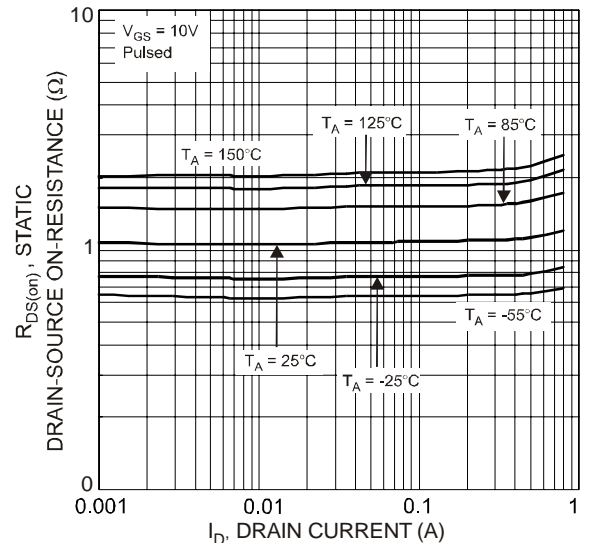


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

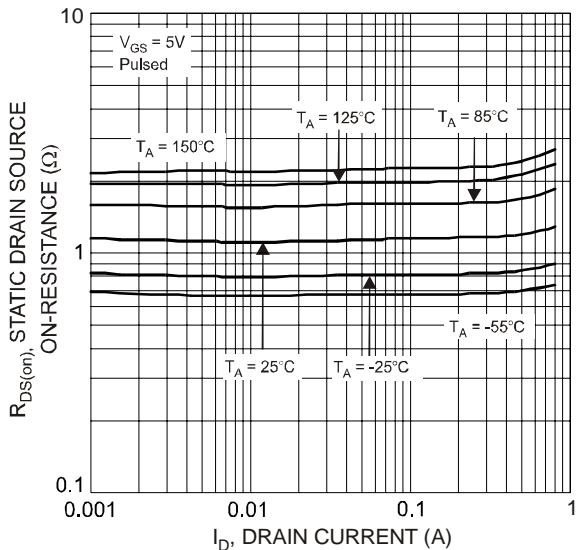


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

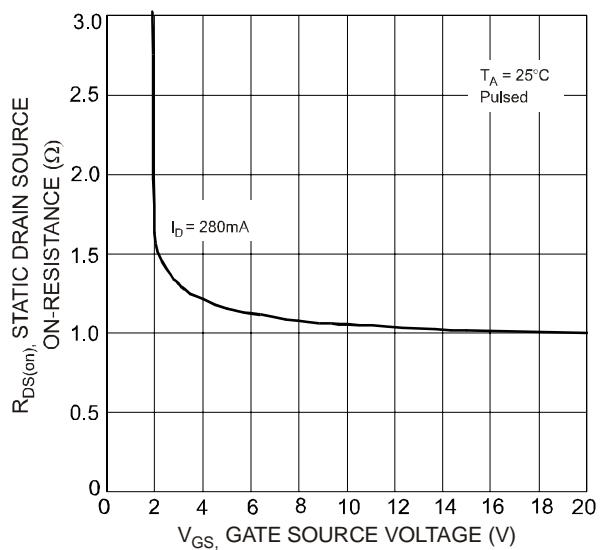


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

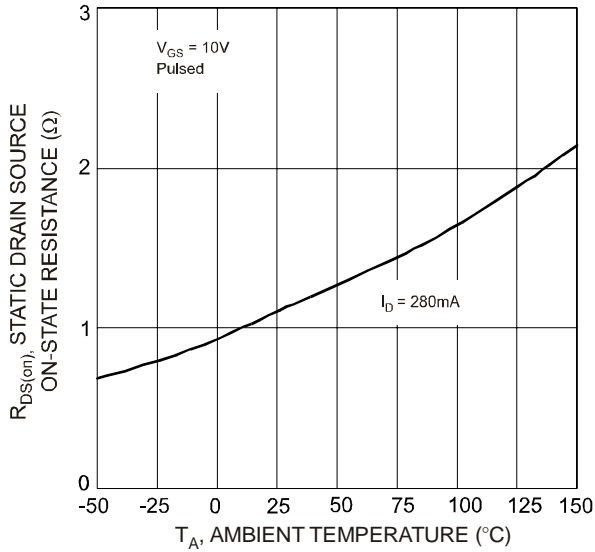


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

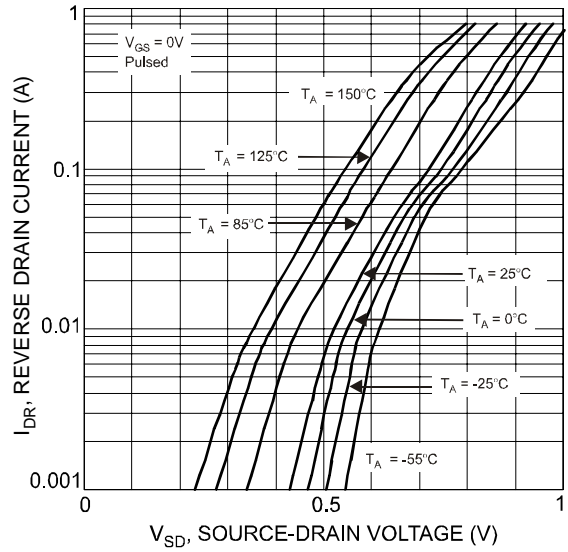


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

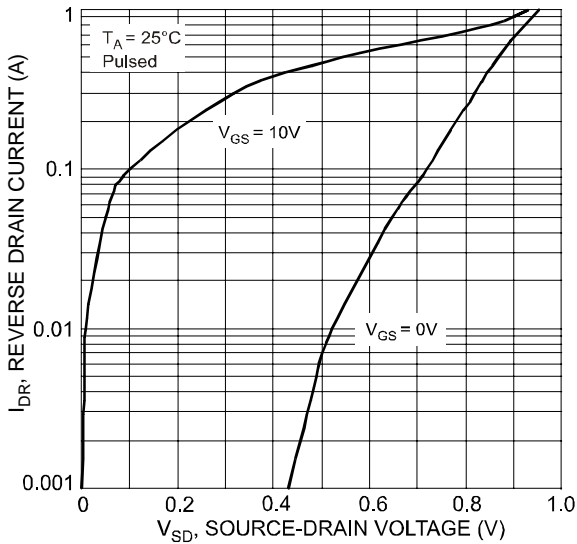


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

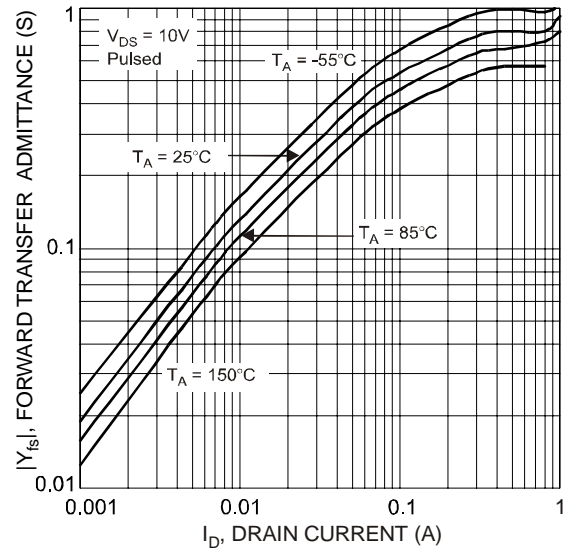


Fig. 10 Forward Transfer Admittance vs. Drain Current

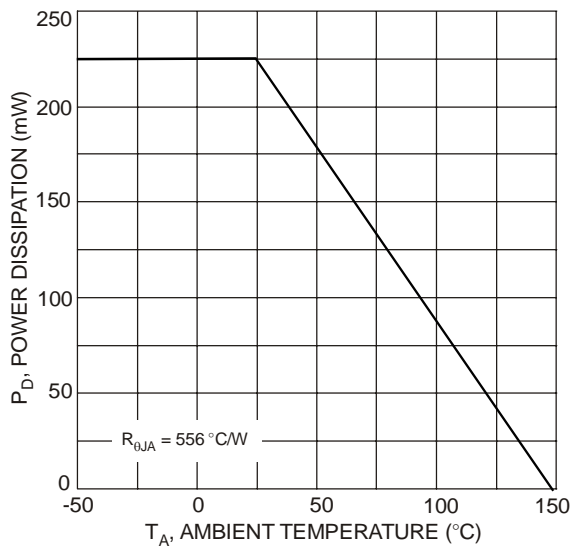


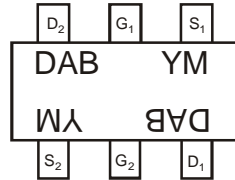
Fig. 11 Derating Curve - Total

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMN5L06DMK-7	SOT-26	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



DAB = Marking Code  
YM = Date Code Marking  
Y = Year ex: T = 2006  
M = Month ex: 9 = September

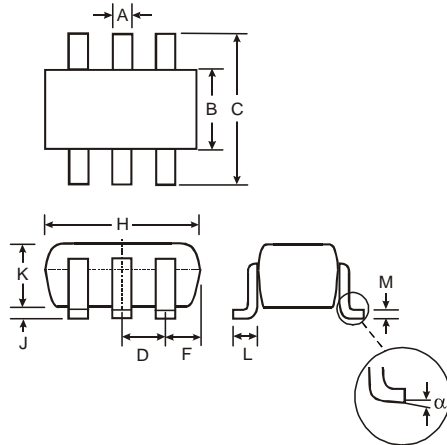
**Date Code Key**

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

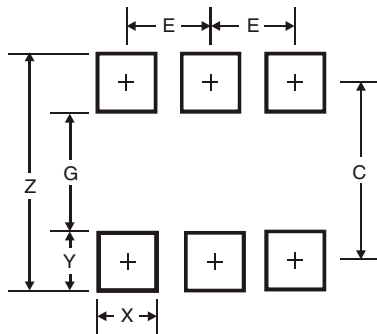
**Package Outline Dimensions**



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	-	-	0.95
F	-	-	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	-

All Dimensions in mm

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

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